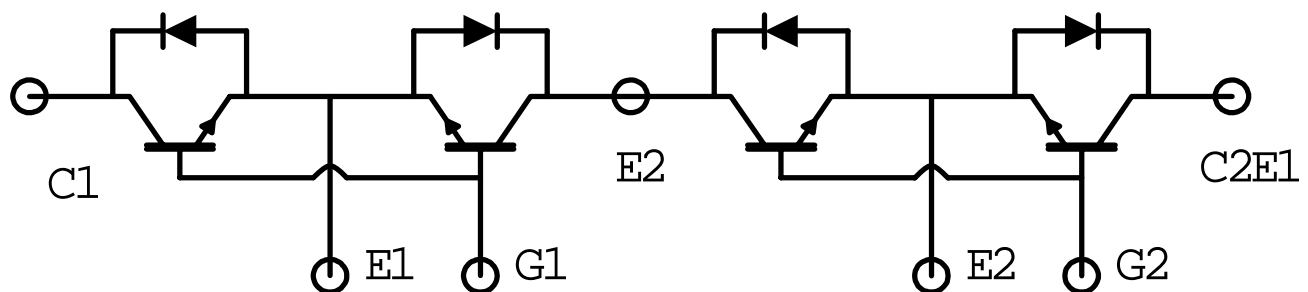


**Description:**  
Powerex Dual AC Switch IGBT Module designed specially for customer applications.

**Features:**

- Isolated Mounting
- Low Drive Requirement
- Internal Series Gate Resistors
- Low Vce(sat)
- Rectifier Grade Low Vf Diodes

Dim	Inches	Millimeters
A	3.70	94.0
B	3.150 ±0.01	80.0 ±0.25
C	1.89	48.0
D	1.18 Max.	30.0 Max
E	0.90	23.0
F	0.83	21.2
G	0.71	18.0
H	0.67	17.0
J	0.63	16.0
K	0.51	13.0
L	0.47	12.0
M	0.30	7.5
N	0.28	7.0
P	0.256 Dia.	Dia. 6.5
Q	0.26	6.5
R	---	M5
S	0.16	4.0

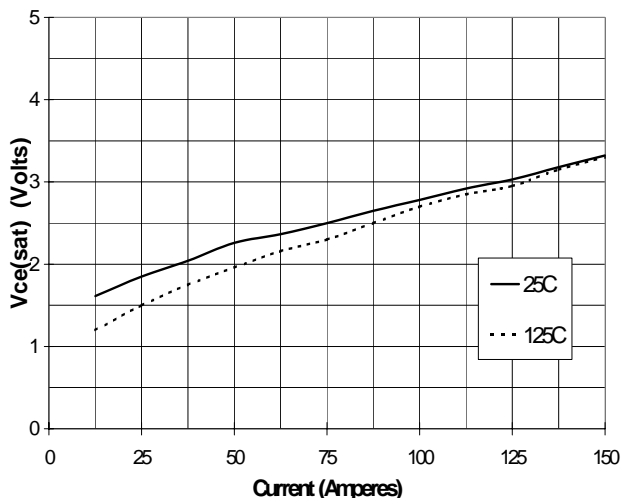


## Electrical Characteristics

### Characteristics (Each IGBT or Each Diode)

Symbol	Parameter	Min	Typ.	Max.	Units
<b>IGBT</b>					
$V_{CES}$	Collector Emitter Voltage (G-E SHORT)	1200			V
$V_{GES}$	Gate Emitter Voltage			K20	V
$I_{GES}$	Gate Leakage Current $V_{GE}=V_{GES}$ $V_{CE}=0$			0.5	$\mu$ A
$I_{CES}$	Collector-Cutoff Current $V_{CE}=600V$ $V_{GE}=0$			1	mA
$V_{GE(th)}$	Gate Emitter Threshold Voltage $I_C=7.5mA$ $V_{CE}=10V$	4.5	6.0	7.5	V
$C_{IES}$	Input Capacitance $V_{CE}=10V$ $V_{GE}=0$ $f=1Mhz$		15		nF
$C_{OES}$	Output Capacitance $V_{CE}=10V$ $V_{GE}=0$ $f=1Mhz$		5.3		nF
$C_{RES}$	Reverse Transfer Capacitance $V_{CE}=10V$ $V_{GE}=0$ $f=1Mhz$		3		nF
$R_{th(j-c)}$	Thermal Impedance Junction to case (Per IGBT)		0.21		C/W
<b>DIODE</b>					
$R_{th(j-c)}$	Thermal Impedance Junction to case (Per Diode)		0.30		C/W
<b>PACKAGE</b>					
$V_{rms}$	V Isolation			2500	V
	Module weight		190		g
	Mounting torque M6 Mounting screw			4	Nm
	Terminal torque, M6 Terminal Screw			6	Nm
$R_{th(jc-s)}$	Thermal Impedance Case to Sink			0.08	C/W

Typical IGBT Collector-Emitter Saturation Voltage



Typical Diode Vf

